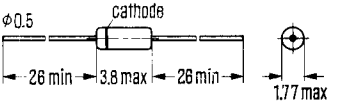
Silicon planar logical diode

BAW 75 is a silicon planar diode in "double heat sink" technique in a case 56 A 2 DIN 41883 (DO-35). The cathode is marked by a green colour ring. BAW 75 is particularly suitable for use as high-speed switch in computers as well as for general switching applications. Its low capacitance and limited spread in electrical data offer a high degree of reliability. BAW 75 is the follower type to BAY 60 and is similar to the diode 1 N 4154.

Type	Order number
BAW 75	Q62702-A396



Weight approx. 0.18 g Dimensions in mm

Type BAW 75 may be marked either by clear coding or by colour rings (red, blue, violet, green)

Maximum ratings ($T_{amb}=25$ °C)		**BAW 75**	
Reverse voltage	V_R	35	V
Rectified current ($t_{av}<50$ ms)	I_O	150	mA
Forward current	I_F	300	mA
Maximum forward current	i_{FM}	500	mA
Impulse current ($t<1$ µs)	i_{FS}	2	A
Junction temperature	T_j	200	°C
Ambient temperature	T_{amb}	−65 to +200	°C
Total power dissipation ($T_{amb}=25$ °C)	P_{tot}	500	mW

Static characteristics ($T_{amb}=25$ °C)			
Forward voltage ($I_F=30$ mA)	V_F	≦1.0*	V
Reverse current ($V_R=35$ V)	I_R	≦5	µA
Reverse current ($V_R=25$ V)	I_R	≦0.1*	µA
Reverse current ($V_R=25$ V; $T_{amb}=150$ °C)	I_R	≦100	µA

Dynamic characteristics ($T_{amb}=25$ °C)			
Capacitance ($V_R=0$ V)	C_O	≦4	pf
Reverse recovery time ($I_F=I_R=10$ mA; recovery to 1 mA)	t_{rr}	≦4	ns
Reverse recovery time ($I_F=10$ mA; $V_R=6$ V; $R_L=100$ Ω)	t_{rr}	≦2	ns

* AQL = 0.65%